

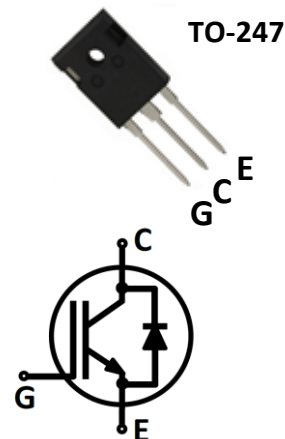


## 特征

高可靠性及热稳定性，良好的参数一致性  
低关断损耗  
饱和压降为正温度系数，易于并联使用  
内置快恢复二极管

## 应用领域

逆变焊机



## 最大额定值<sup>1)</sup>

参数	符号	额定值	单位
集电极-发射极电压	$V_{CE}$	1200	V
集电极电流 $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	$I_C$	50 25	A
集电极脉冲电流	$I_{Cpuls}$	75* <sup>2)</sup>	
RBSOA电流 $V_{CE}<1200\text{V}, T_J<150^{\circ}\text{C}$	$I_{Cpeak}$	75*	
二极管正向电流 $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	$I_F$	30 <sup>3)</sup> 15	
二极管脉冲电流	$I_{Fpuls}$	45*	
栅极-发射极电压	$V_{GE}$	$\pm 20$	V
耗散功率 $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	$P_{tot}$	255 102	W
工作结温	$T_J$	-55~150	$^{\circ}\text{C}$
储存温度	$T_{stg}$	-55~150	

<sup>1)</sup>测试标准参考JESD-022

<sup>2)</sup>加\*表示估计值，下同

<sup>3)</sup>受限于邦定线

## 热学特性

参数	符号	封装形式	最小值	典型值	最大值	单位
IGBT结壳热阻	$R_{thJC}$	TO-247	-	-	0.49	K/W
二极管结壳热阻	$R_{thJD}$	TO-247	-	-	1.2	
结-环境热阻	$R_{thJA}$	TO-247	-	-	40	

## 电学特性 (未特殊说明时, $T_j=25^\circ\text{C}$ )

参数	符号	测试条件	最小值	典型值	最大值	单位
<b>静态特性</b>						
击穿电压	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	1200	-	-	V
IGBT导通压降	$V_{CE(sat)}$	$V_{GE}=15V, I_C=25A$ $T_j=25^\circ\text{C}$	-	2.30	2.60	
		$T_j=150^\circ\text{C}$	-	2.60	-	
二极管正向压降	$V_F$	$V_{GE}=0V, I_F=25A$ $T_j=25^\circ\text{C}$	-	2.50	-	
		$T_j=150^\circ\text{C}$	-	2.75	-	
阈值电压	$V_{GE(th)}$	$I_C=1mA, V_{CE}=V_{GE}$	5.0	6.1	7.0	mA
集电极-发射极漏电流	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ\text{C}$	-	-	0.1	
		$T_j=150^\circ\text{C}$	-	-	2.0	
栅极-发射极漏电流	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
跨导	$g_{FS}$	$V_{CE}=20V, I_C=25A$	-	10.5	-	S
<b>动态特性</b>						
输入电容	$C_{iss}$	$V_{CE}=25V$	-	3480	-	pF
输出电容	$C_{oss}$	$V_{GE}=0V$	-	99	-	
反馈电容	$C_{rss}$	$f=1MHz$	-	58	-	
栅电荷	$Q_G$	$V_{CC}=900V, I_C=25A, V_{GE}=15V$	-	tbd	-	nC

参数	符号	测试条件	最小值	典型值	最大值	单位
IGBT开关特性（感性负载）						
开通延迟时间	$t_{d(on)}$	$T_j=25^{\circ}\text{C}$ $V_{CC}=600\text{V}, I_C=25\text{A}$ $V_{GE}=15/0\text{V}$ $R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	45	-	ns
上升时间	$t_r$		-	50	-	
关断延迟时间	$t_{d(off)}$		-	165	-	
下降时间	$t_f$		-	98	-	
开通损耗	$E_{on}$		-	1.33	-	mJ
关断损耗	$E_{off}$		-	0.82	-	
开关损耗	$E_{ts}$		-	2.15	-	
开通延迟时间	$t_{d(on)}$	$T_j=150^{\circ}\text{C}$ $V_{CC}=600\text{V}, I_C=25\text{A}$ $V_{GE}=15/0\text{V}$ $R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	35	-	ns
上升时间	$t_r$		-	52	-	
关断延迟时间	$t_{d(off)}$		-	200	-	
下降时间	$t_f$		-	225	-	
开通损耗	$E_{on}$		-	1.35	-	mJ
关断损耗	$E_{off}$		-	1.60	-	
开关损耗	$E_{ts}$		-	2.95	-	
二极管开关特性						
反向恢复时间	$t_{rr}$	$T_j=25^{\circ}\text{C}$ $V_R=600\text{V}, I_F=25\text{A}$ $di_F/dt=600\text{A}/\mu\text{s}$	-	115	-	ns
反向恢复电荷	$Q_{rr}$		-	1.60	-	$\mu\text{C}$
反向恢复峰值电流	$I_{rrm}$		-	23.0	-	A
反向恢复时间	$t_{rr}$	$T_j=150^{\circ}\text{C}$ $V_R=600\text{V}, I_F=25\text{A}$ $di_F/dt=600\text{A}/\mu\text{s}$	-	180	-	ns
反向恢复电荷	$Q_{rr}$		-	2.20	-	$\mu\text{C}$
反向恢复峰值电流	$I_{rrm}$		-	25.0	-	A

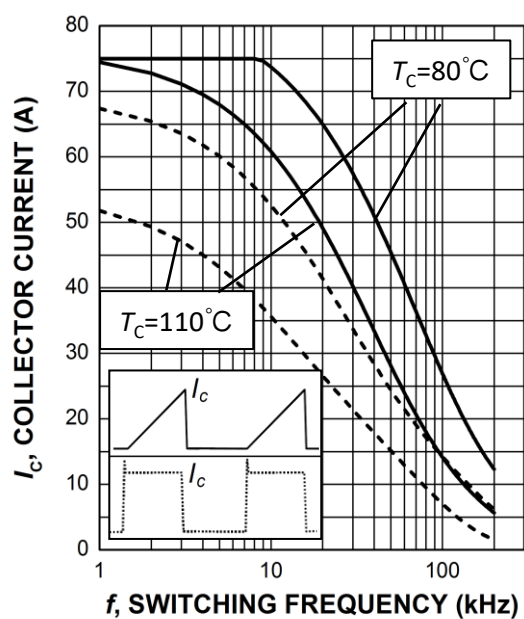


Figure 1. Collector current as a function of switching frequency

( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 600\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 15\Omega$ )

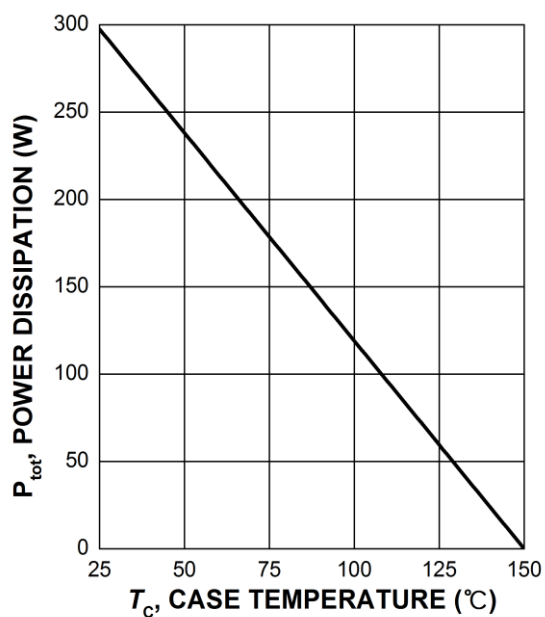


Figure 2. Maximum power dissipation as a function of case temperature

( $T_j \leq 150^\circ\text{C}$ )

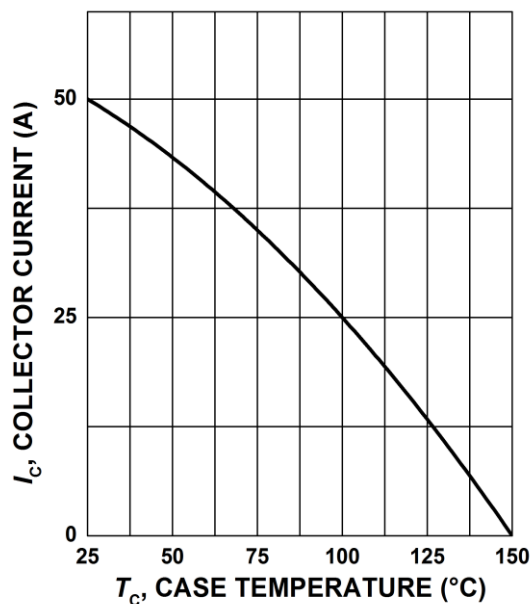


Figure 3. Maximum collector current as a function of case temperature

( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )

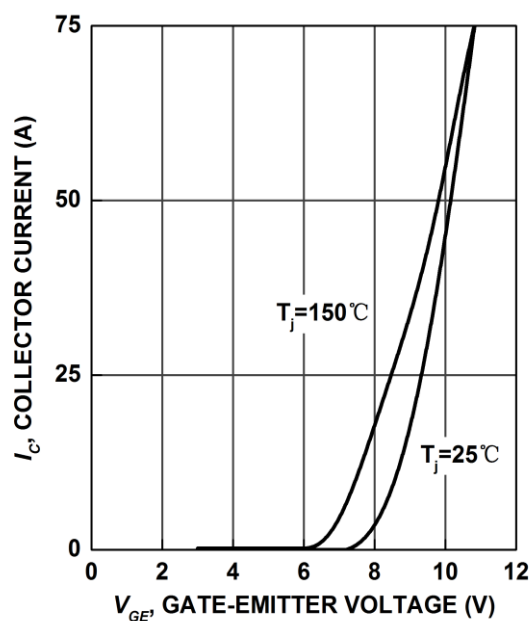


Figure 4. Typical transfer characteristic

( $V_{CE} = 15\text{V}$ )

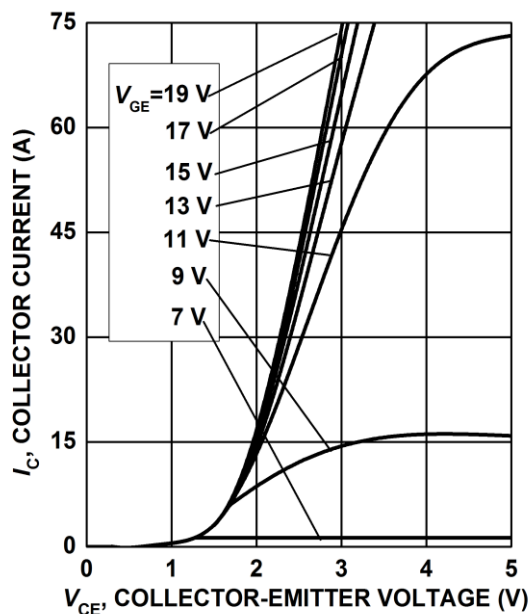


Figure 5. Typical output characteristic  
( $T_j = 25^\circ\text{C}$ )

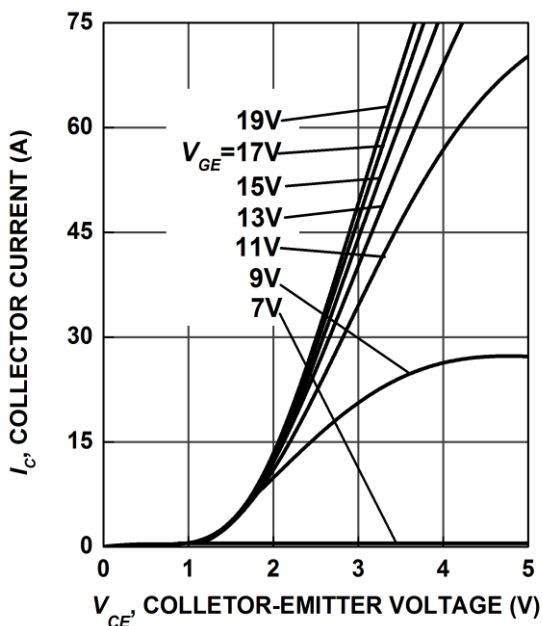


Figure 6. Typical output characteristic  
( $T_j = 150^\circ\text{C}$ )

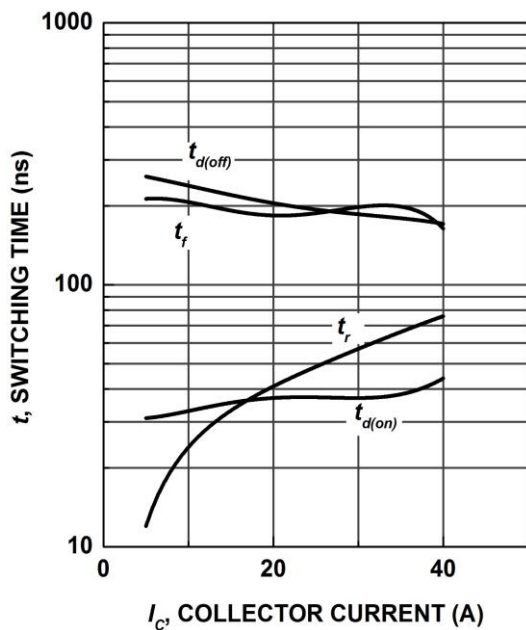


Figure 7. Typical switching times as a function of collector current  
(inductive load,  $T_j=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=15\Omega$ ,  
Dynamic test circuit in Figure D)

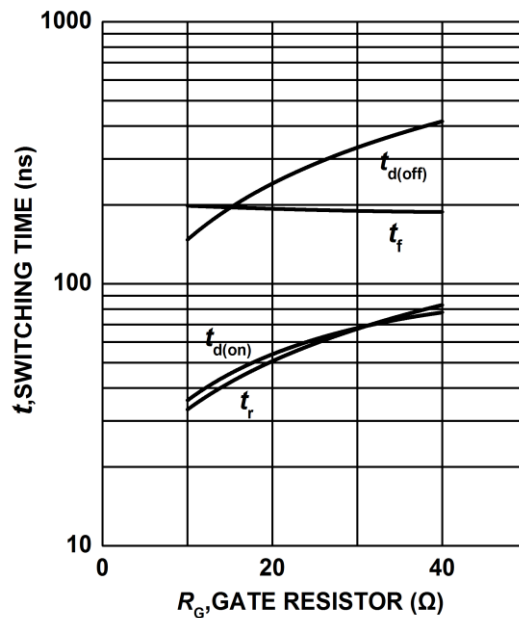


Figure 8. Typical switching times as a function of gate resistor  
(inductive load,  $T_j=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=25\text{A}$ , Dynamic test circuit in  
Figure D)

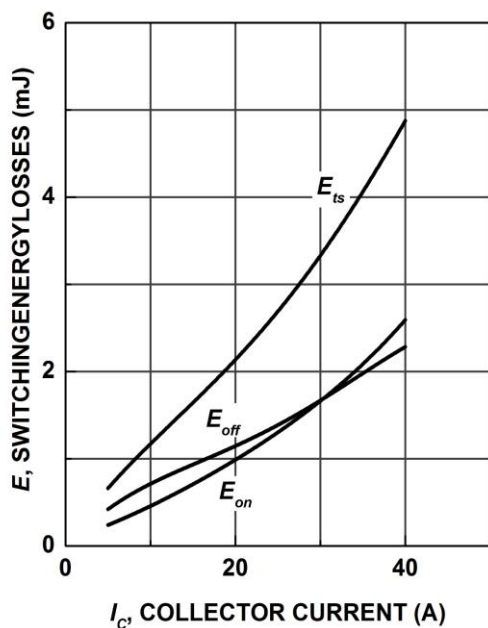


Figure 9. Typical switching energy losses as a function of collector current  
(inductive load,  $T_j=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  
 $V_{GE}=0/15\text{V}$ ,  $R_G=15\Omega$ ,  
Dynamic test circuit in Figure D)

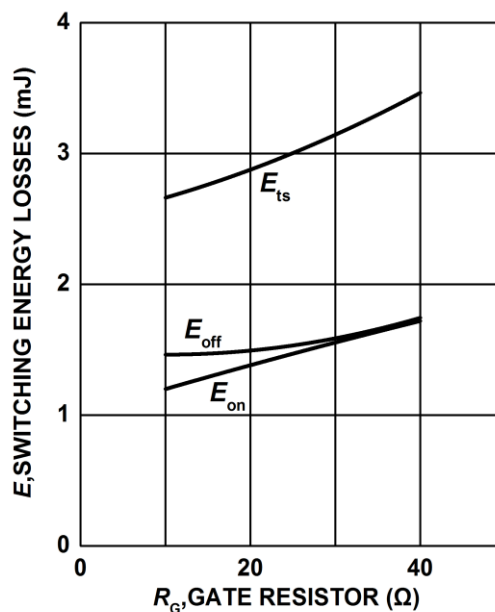


Figure 10. Typical switching energy losses as a function of gate resistor  
(inductive load,  $T_j=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  
 $V_{GE}=0/15\text{V}$ ,  $I_C=25\text{A}$ ,  
Dynamic test circuit in Figure D)

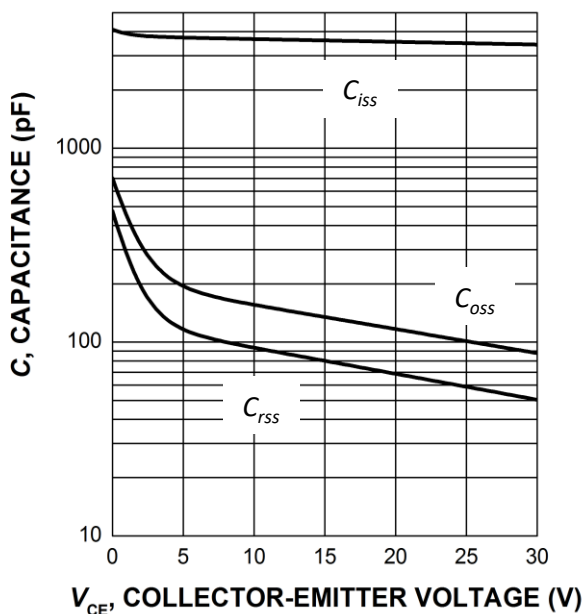


Figure 11. Typical capacitance as a function of collector-emitter voltage  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )

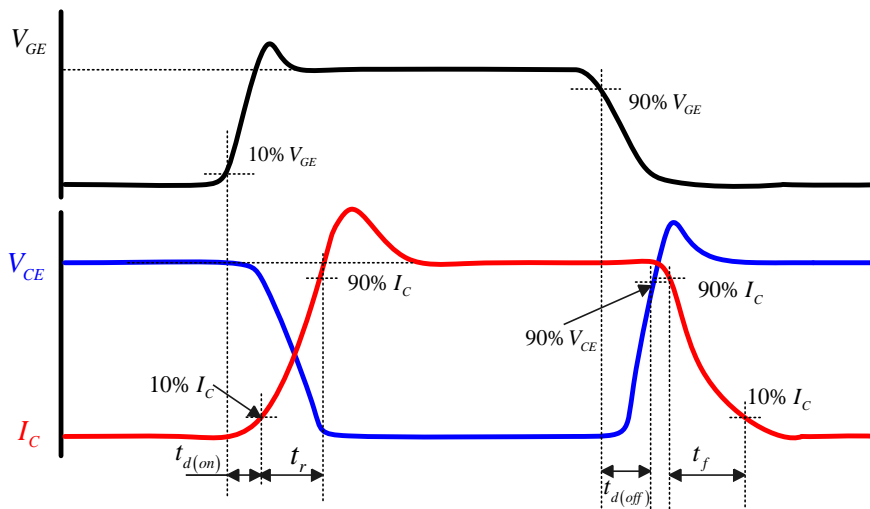


Figure A. Definition of switching times

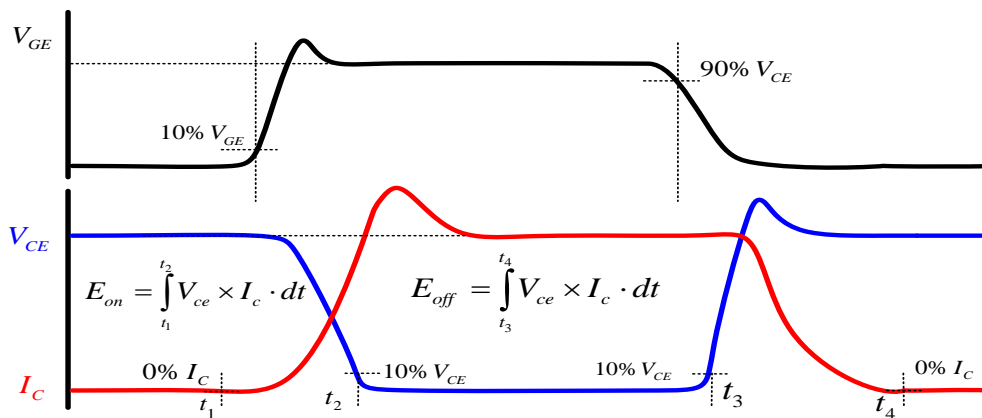


Figure B. Definition of switching losses

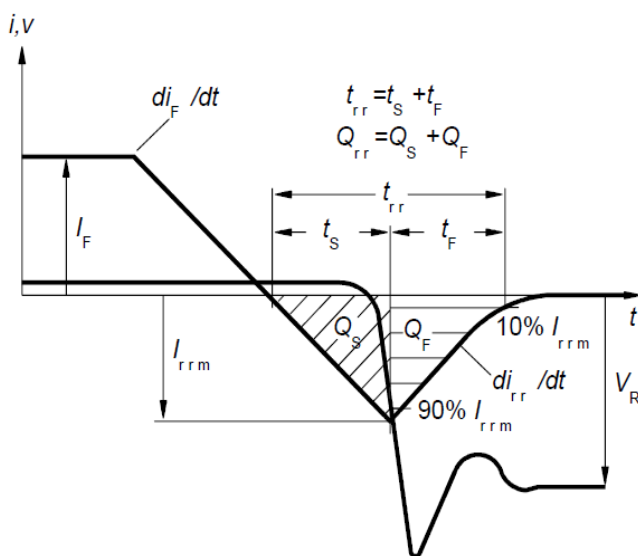


Figure C. Definition of diodes switching characteristics

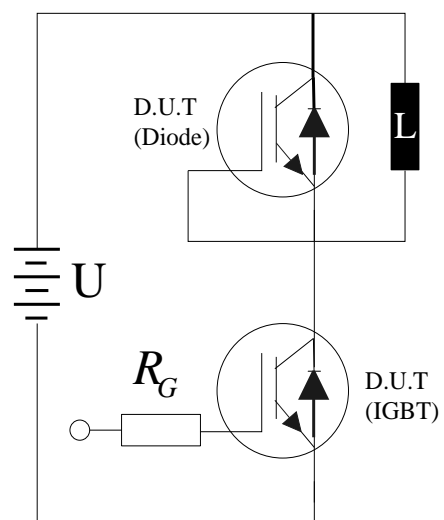
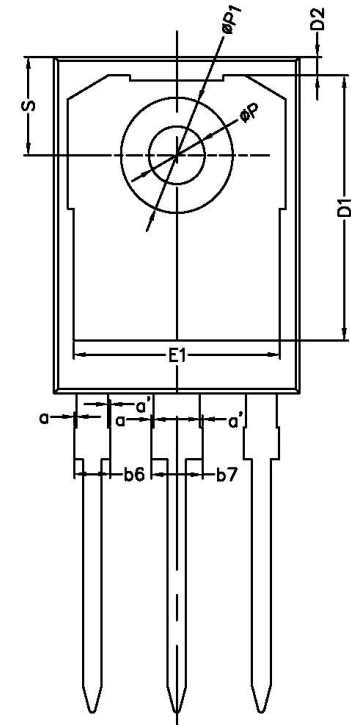
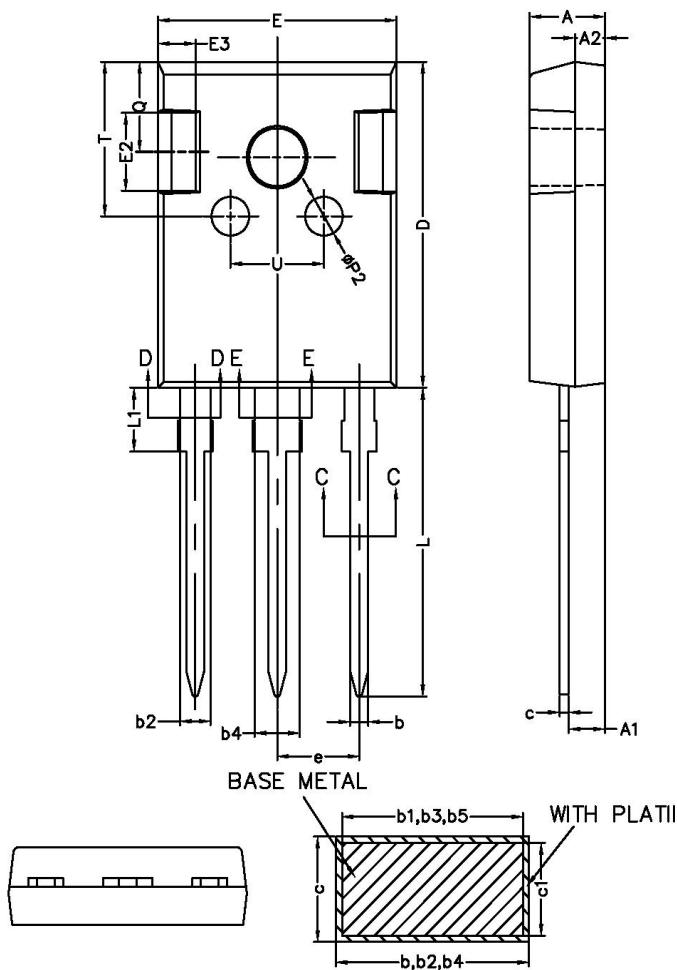


Figure D. Dynamic test circuit

## TO-247



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
$\Delta$ a	0	—	0.15
$\Delta$ a'	0	—	0.15
b	1.16	—	1.26
b1	1.15	1.2	1.22
b2	1.96	—	2.06
b3	1.95	2.00	2.02
b4	2.96	—	3.06
b5	2.95	3.00	3.02
$\Delta$ b6	—	—	2.25
$\Delta$ b7	—	—	3.25
c	0.59	—	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
$\Delta$ e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1	—	—	4.30
P	3.50	3.60	3.70
P1	—	—	7.40
P2	2.40	2.50	2.60
Q	5.60	—	6.00
$\Delta$ S	6.05	6.15	6.25
T	9.80	—	10.20
U	6.00	—	6.40

NOTES:  
1. ALL DIMENSIONS REFER TO JEDEC STANDARD  
TO-247 AD DO NOT INCLUDE MOLD FLASH  
OR PROTRUSIONS.  
2. EJECTION MARK DEPTH  $0.10^{+0.15}_{-0.05}$ .